

1. General description

Dual Silicon Carbide Schottky diode in a TO247 plastic package, designed for high frequency switched-mode power supplies.



Lead-Free

2. Features and benefits

- Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

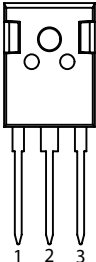
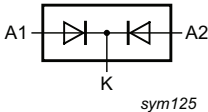
Table 1. Quick reference data

Table 11. Quick reference data

| Symbol | Parameter | Conditions | Notes | Values | | | Unit |
|-------------------------|----------------------------------|---|-------|------------|------|------|------|
| Absolute maximum rating | | | | | | | |
| V _{RRM} | repetitive peak reverse voltage | | | 650 | | | V |
| I _{O(AV)} | limiting average forward current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 101 °C; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3 | | 30 | | | A |
| T _j | junction temperature | | | -55 to 175 | | | °C |
| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
| Static characteristics | | | | | | | |
| V _F | forward voltage | I _F = 15 A; T _j = 25 °C; per diode; Fig. 5 | | - | 1.45 | 1.70 | V |
| | | I _F = 15 A; T _j = 150 °C; per diode; Fig. 5 | | - | 1.80 | 2.20 | V |
| Dynamic characteristics | | | | | | | |
| Q _r | recovered charge | I _F = 15 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; per diode; Fig. 7 | | - | 24 | - | nC |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|---|---|
| 1 | A1 | anode |  |  |
| 2 | K | cathode | | |
| 3 | A2 | anode | | |
| mb | mb | mounting base; connected to cathode | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|---------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WNSC5D30650CW | TO247 | WNSC5D30650CW6Q | Tube | 30 | TO247N | 20-July-2016 |

7. Marking

Table 4. Marking codes

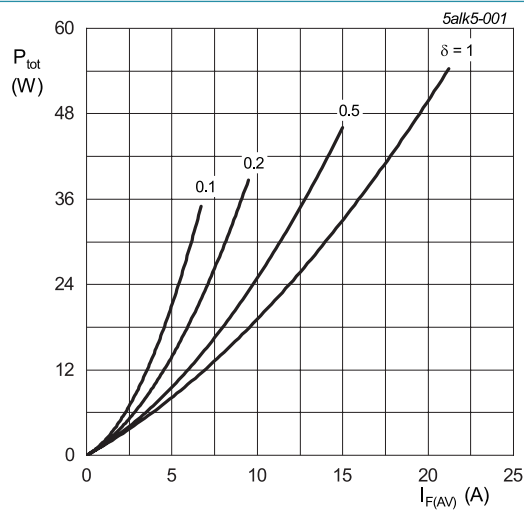
| Type number | Marking codes |
|---------------|-------------------|
| WNSC5D30650CW | WNSC5D 30650CW |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Notes | Values | Unit |
|-------------|-------------------------------------|--|-------|------------|----------------------|
| V_{RRM} | repetitive peak reverse voltage | | | 650 | V |
| V_{RWM} | crest working reverse voltage | | | 650 | V |
| V_R | reverse voltage | DC | | 650 | V |
| $I_{O(AV)}$ | limiting average forward current | $\delta = 0.5$; square-wave pulse; $T_{mb} \leq 101\text{ }^{\circ}\text{C}$; both diodes conducting; Fig. 1; Fig. 2; Fig. 3 | | 30 | A |
| I_{FRM} | repetitive peak forward current | $\delta = 0.5$; $t_p = 25\text{ }\mu\text{s}$; $T_{mb} \leq 111\text{ }^{\circ}\text{C}$; square-wave pulse; per diode | | 30 | A |
| I_{FSM} | non-repetitive peak forward current | $t_p = 10\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; sine-wave pulse; per diode | | 85 | A |
| | | $t_p = 10\text{ }\mu\text{s}$; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; square-wave pulse; per diode | | 800 | A |
| I^2t | I^2t for fusing | sine-wave pulse; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$ | | 36.125 | A^2s |
| T_{stg} | storage temperature | | | -55 to 175 | $^{\circ}\text{C}$ |
| T_j | junction temperature | | | -55 to 175 | $^{\circ}\text{C}$ |



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.334\text{ V}; R_s = 0.0578\text{ }\Omega$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

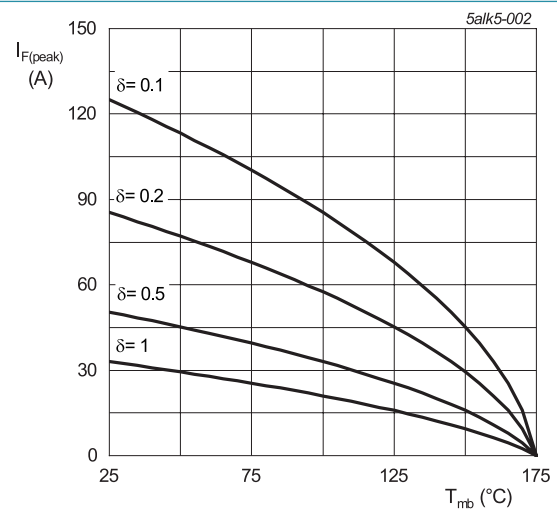


Fig. 2. Current derating as a function of mounting base temperature; per diode

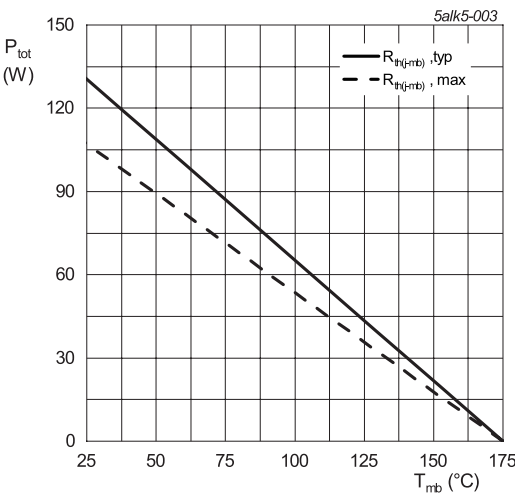


Fig. 3. Total power dissipation as a function of mounting base temperature; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
|----------------|--|-----------------------------------|-------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | per diode; Fig. 4 | | - | 1.15 | 1.4 | K/W |
| | | both diodes conducting | | - | 0.6 | 0.75 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | | - | 60 | - | K/W |

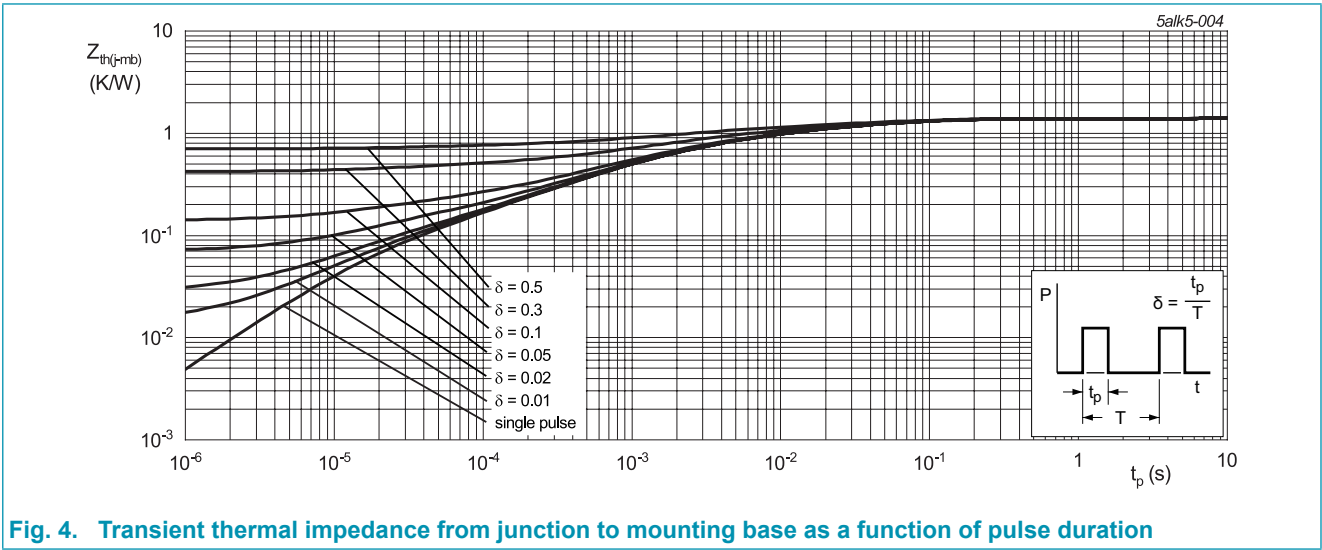
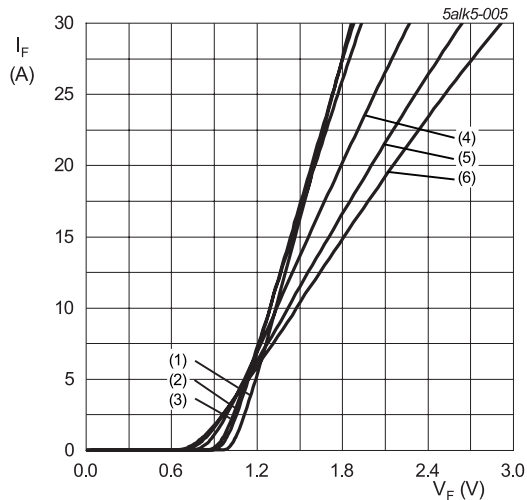


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
|-------------------------|---------------------------------|--|-------|-----|------|------|------|
| Static characteristics | | | | | | | |
| V _F | forward current | I _F = 15 A; T _j = 25 °C; per diode; Fig. 5 | | - | 1.45 | 1.70 | V |
| | | I _F = 15 A; T _j = 150 °C; per diode; Fig. 5 | | - | 1.80 | 2.20 | V |
| | | I _F = 15 A; T _j = 175 °C; per diode; Fig. 5 | | - | 2.00 | 2.30 | V |
| I _R | reverse current | V _R = 650 V; T _j = 25 °C; per diode; Fig. 6 | | - | 1 | 50 | μA |
| | | V _R = 650 V; T _j = 175 °C; per diode; Fig. 6 | | - | 25 | 350 | μA |
| Dynamic characteristics | | | | | | | |
| Q _r | recovered charge | I _F = 15 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 25 °C; per diode; Fig. 7 | | - | 24 | - | nC |
| C _d | diode capacitance | f = 1 MHz; V _R = 1 V; T _j = 25 °C; per diode | | - | 500 | - | pF |
| | | f = 1 MHz; V _R = 300 V; T _j = 25 °C; per diode | | - | 58 | - | pF |
| | | f = 1 MHz; V _R = 600 V; T _j = 25 °C; per diode | | - | 52 | - | pF |
| E _{as} | non-repetitive avalanche energy | I _R = 5 A; L = 5 mH; T _{j(init)} = 25 °C; per diode | | 60 | - | - | mJ |



$V_o = 1.334\text{ V}$; $R_s = 0.0578\text{ }\Omega$

- (1) $T_J = -55\text{ }^\circ\text{C}$; typical values
- (2) $T_J = 0\text{ }^\circ\text{C}$; typical values
- (3) $T_J = 25\text{ }^\circ\text{C}$; typical values
- (4) $T_J = 100\text{ }^\circ\text{C}$; typical values
- (5) $T_J = 150\text{ }^\circ\text{C}$; typical values
- (6) $T_J = 175\text{ }^\circ\text{C}$; typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

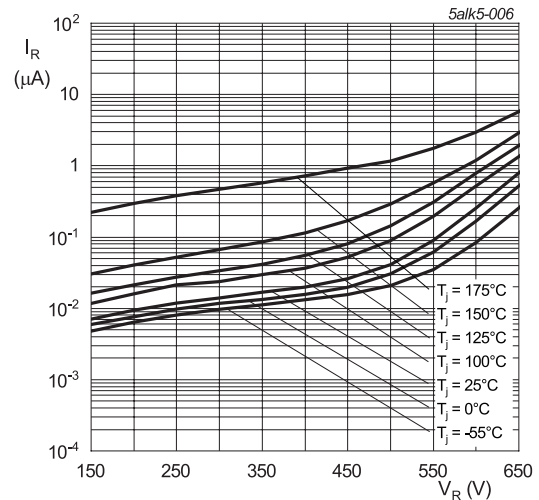


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

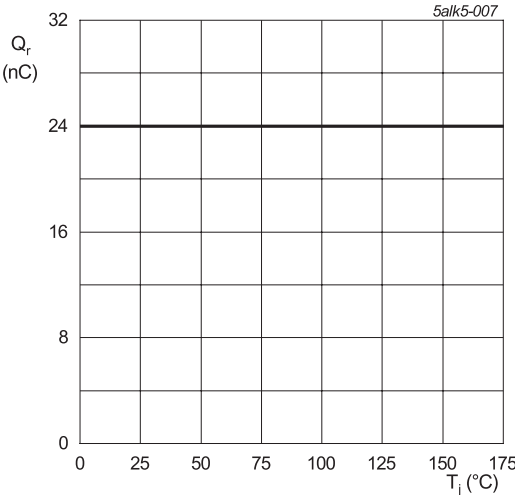
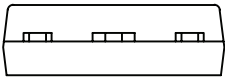
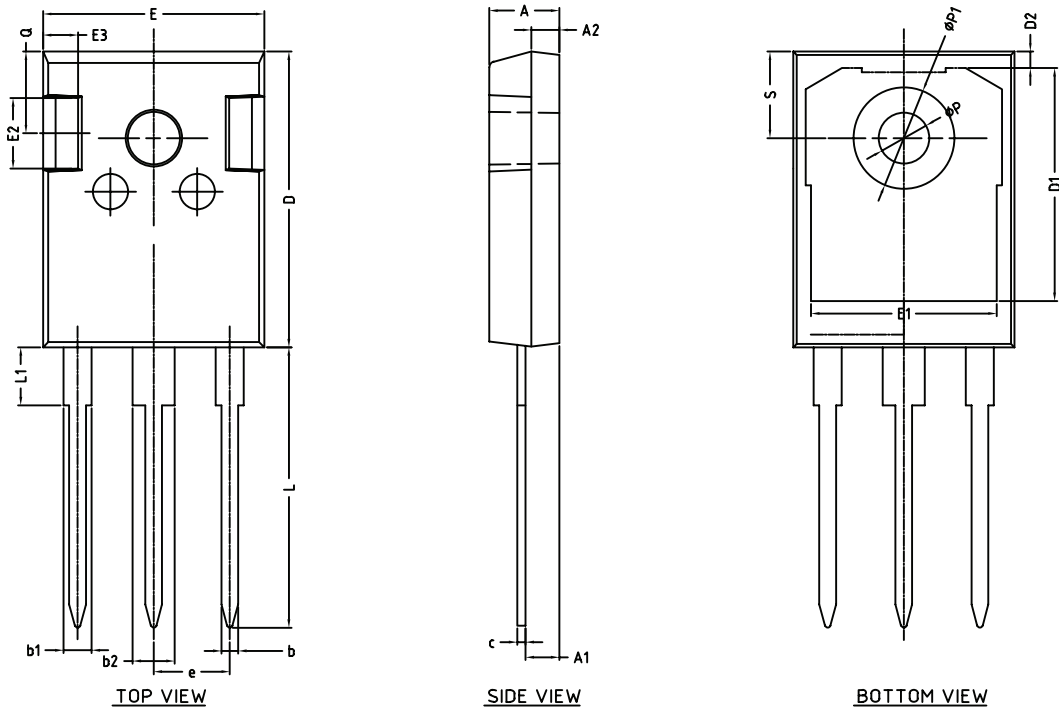


Fig. 7. Recovered charge as a function of junction temperature; per diode

11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247 SOT429N



SIDE VIEW

| UNIT | A | A1 | A2 | b | b1 | b2 | c | D | D1 | D2 | E | E1 | E2 | E3 | e | L | L1 | P | P1 | Q | S |
|------|-----|------|------|------|------|------|------|------|-------|-------|------|-------|-------|------|------|-------|------|------|------|------|------|
| mm | MAX | 5.20 | 2.60 | 2.10 | 1.40 | 2.20 | 3.20 | 0.70 | 21.10 | 16.85 | 1.35 | 15.90 | 13.50 | 5.20 | 2.60 | 20.10 | 4.75 | 3.70 | 7.40 | 6.00 | 6.25 |
| | NOM | | | | | | | | | | | | | | | | | | | | |
| | MIN | 4.70 | 2.20 | 1.90 | 1.00 | 1.80 | 2.80 | 0.50 | 20.90 | 16.25 | 1.05 | 15.70 | 13.10 | 4.80 | 2.40 | 19.80 | - | 3.50 | - | 5.60 | 6.05 |

| OUTLINE VERSION | REFERENCES | | | | PROJECTION | ISSUE DATE |
|--------------------|------------|--------|-------|--|------------|------------|
| | IEC | JEDEC | EIA J | | | |
| SOT429N | | TO-247 | | | | |

12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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